

Specification of 2" GaAs (Undoped) Wafer

Description	Specification
Growth Method	VGF
Dopant	Undoped (Semi-insulating)
Resistivity	$\geq 1.0E7$ ohm.cm
Etch Pitch Density	$\leq 6000/cm^2$
Mobility	$\geq 4500cm^2/V.S$
Surface Orientation	(100) $\pm 0.5^\circ$
Pruner Flat Orientation	OF: EJ [0`1`1] $\pm 0.5^\circ$ IF: EJ [0`1`1] $\pm 0.5^\circ$
Primary Flat Length (OF)	16 ± 1 mm
Secondary Flat (IF)	7 ± 1 mm
Diameter	50.7 ± 0.30 mm
Thickness	350 ± 20 um
Double Surface Polishing Roughness	Ra: ≤ 0.3 nm (DSP)
TTV	≤ 10 um
TIR	≤ 10 um
BOW	≤ 10 um
Warp	≤ 10 um
Scratch	None
Defective Patterns	T<50/wafer(for particle>0.3um)
Laser Marking	None or As Substrate NO.
Packaging	Clean room, vacuum packing

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